

Docket No.: L/E 047B/1002
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent Application of:
Mark Gottfried

Parent Application

Application No.: To Be Assigned

Group Art Unit 2812

Filed:

Examiner: L. Gurley

For: METHOD OF MAKING AN ALIGNED
ELECTRODE ON A SEMICONDUCTOR
STRUCTURE (As Amended)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

PRELIMINARY AMENDMENT

Dear Sir:

Prior to examination, please amend the above-identified application as follows:

Application No.: To Be Assigned
AMENDMENTS TO THE SPECIFICATION

Docket No.: L/E 047B/1002

IN THE TITLE

Please amend the title to read:

--METHOD OF MAKING AN ALIGNED ELECTRODE ON A SEMICONDUCTOR
STRUCTURE--

IN THE ABSTRACT

On p.28, cancel the Abstract and substitute:

--A method of making an electrode on a semiconductor device including depositing metal on a top surface of a semiconductor structure, and defining a first region of the semiconductor structure for a first electrode by forming a mask over the metal. The mask has an opening so that the first region is covered by the mask and a second region of the structure is aligned with the opening in the mask. Metal aligned with the opening in the mask in the second region is then removed to form a first electrode overlying the first region of the semiconductor structure, and also revealing the top surface of the semiconductor structure in the second region. Material is then removed from the semiconductor structure aligned with opening in the second region to form a second electrode surface for a second electrode. --

IN THE CLAIMS

Cancel claims 1-41 without prejudice, and substitute new claims 42-57.